

**KS54AHCT 664/665
KS74AHCT****Octal Bus Transceivers
with Parity T-52-3/****Preliminary Specifications****FEATURES**

- Bus Transceivers with Inverting Outputs ('664) or True Outputs ('665)
- Generates a Parity Bit for A Bus and B Bus
- Easily Cascadable
- Internal Active Pull-Ups and Pull-Downs
- Function, pin-out, speed and drive compatibility with 54/74ALS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ($I_{OL} = 24 \text{ mA} @ V_{OL} = 0.5\text{V}$) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS74AHCT: -40°C to +85°C
KS54AHCT: -55°C to +125°C
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

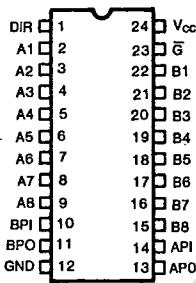
DESCRIPTION

These octal bus transceivers are designed for asynchronous, bidirectional communication between data buses. The devices transmit data from the A Bus to the B Bus or from the B Bus to the A Bus, depending on the level at the direction control input, DIR. The enable input, G, can be used to disable the device so that the buses are isolated. These devices will also generate parity outputs, APO and BPO, which reflect the number of high levels at the A Bus and B Bus, respectively, taking into account the parity inputs API and BPI.

The bidirectional I/O ports feature active circuitry on the input stage that, when the output shared by that pin is disabled, will maintain the input in the last state taken by the output. This state will be maintained until changed by the activity on the bus. The advantage of this arrangement is that when all outputs on the bus are disabled, the inputs will be prevented from floating, resulting in minimum power dissipation and minimum susceptibility to noise. This eliminates any need for external pull-up or pull-down resistors. The parity inputs API and BPI have similar circuitry.

These devices provide speeds and drive capability equivalent to their ALSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

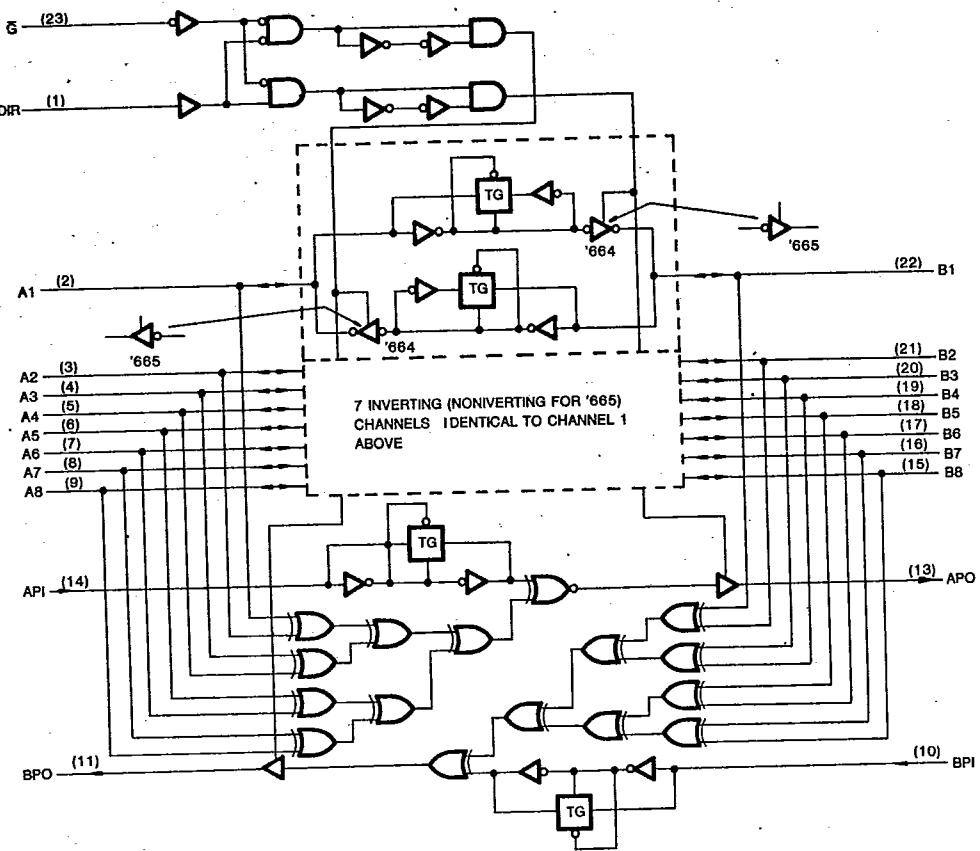
All inputs and outputs are protected from damage due to static discharge by internal diode clamps to Vcc and ground.

PIN CONFIGURATION**FUNCTION TABLE**

CONTROL INPUTS		NUMBER OF HIGH INPUTS ON A BUS AND API	NUMBER OF HIGH INPUTS ON B BUS AND BPI	OUTPUTS		OPERATION	
				APO	BPO	'664	'665
L	L	X	0, 2, 4, 6, 8	Z	H	Ā Data to A Bus	B Data to A Bus
		X	1, 3, 5, 7, 9	Z	L		
L	H	0, 2, 4, 6, 8	X	H	Z	Ā Data to B Bus	A Data to B Bus
		1, 3, 5, 7, 9	X	L	Z		
H	X	X	X	Z	Z	Isolation	Isolation



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**KS54AHCT 664/665
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with Parity****LOGIC DIAGRAM**

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Absolute Maximum Ratings*

Supply Voltage Range V_{cc} -0.5V to +7V
 DC Input Diode Current, I_{IK}
 (V_I < -0.5V or V_I > V_{cc} +0.5V) ±20 mA
 DC Output Diode Current, I_{OK}
 (V_O < -0.5V or V_O > V_{cc} +0.5V) ±20 mA
 Continuous Output Current Per Pin, I_O
 (-0.5V < V_O < V_{cc} +0.5V) ±70 mA
 Continuous Current Through
 V_{cc} or GND pins ±250 mA
 Storage Temperature Range, T_{STG} -65°C to +150°C
 Power Dissipation Per Package, P_D[†] 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:
 Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{cc} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN}, V_{OUT} 0V to V_{cc}
 Operating Temperature Range

KS74AHCT: -40°C to +85°C
 KS54AHCT: -55°C to +125°C

Input Rise & Fall Times, t_r, t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{cc} or GND)



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DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V\pm10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a = 25^\circ C$		KS74AHCT	KS54AHCT	Unit
			Typ		$T_a = -40^\circ C$ to $+85^\circ C$	$T_a = -55^\circ C$ to $+125^\circ C$	
Minimum High-Level Input Voltage	V_{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V_{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IH}$ or V_{IL} $I_O=-20\mu A$ $I_O=-6mA$	V_{CC} 4.2	$V_{CC}-0.1$ 3.98	$V_{CC}-0.1$ 3.84	$V_{CC}-0.1$ 3.7	V
Maximum Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$ or V_{IL} $I_O=20\mu A$ $I_O=12mA$ $I_O=24mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I_{IN}	$V_{IN}=V_{CC}$ or GND		± 0.1	± 1.0	± 1.0	μA
Maximum 3-State Leakage Current	I_{OZ}	Output Enable $=V_{IH}$ $V_{OUT}=V_{CC}$ or GND		± 0.5	± 5.0	± 10.0	μA
Maximum Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI_{CC}	per input pin $V_I=2.4V$ other Inputs: at V_{CC} or GND $I_{OUT}=0\mu A$		2.7	2.9	3.0	mA



**KS54AHCT 664/665
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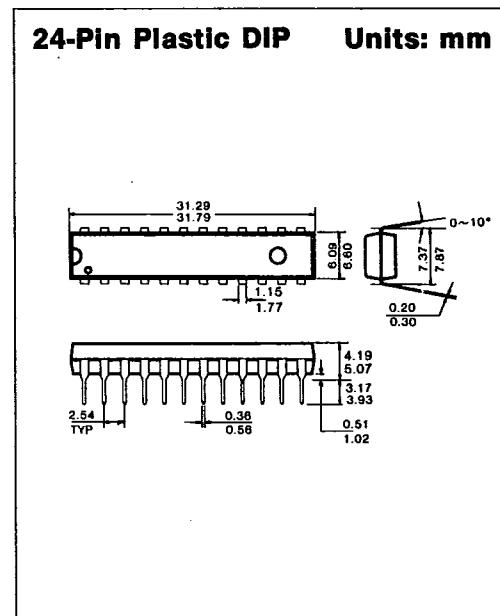
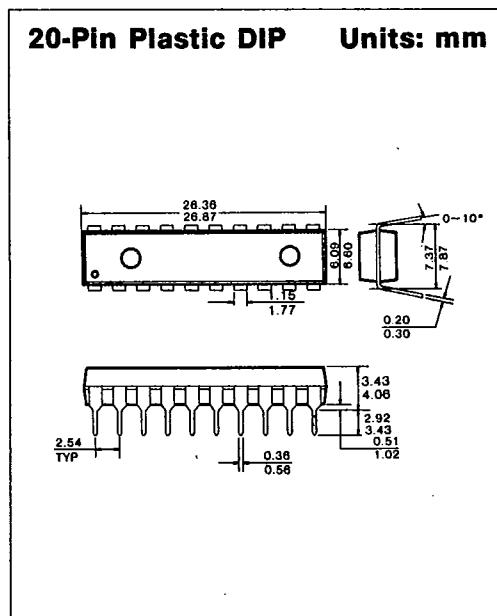
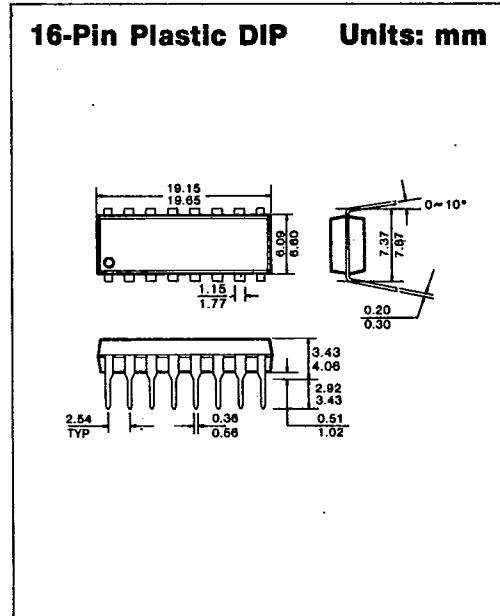
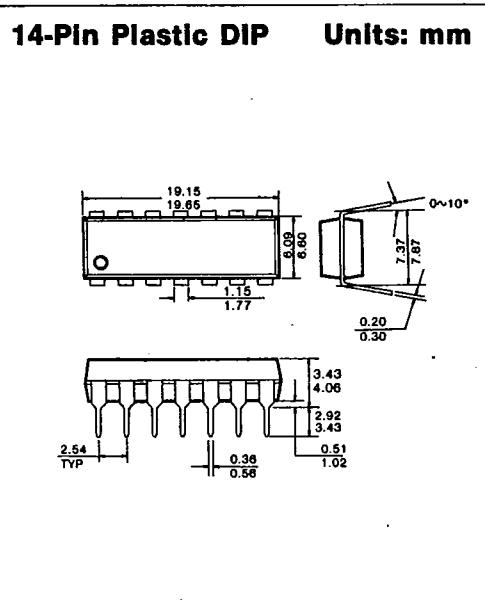
Characteristic	Symbol	Conditions [†]	T _A = 25°C V _{CC} = 5.0V	KS74AHCT		KS54AHCT		Unit
				Typ	Min	Max	Min	
Propagation Delay, A or B to B or A	t _{PLH}	C _L = 50pF C _L = 150pF	11 14		18 23		22 28	ns
	t _{PHL}	C _L = 50pF C _L = 150pF	11 14		18 23		22 28	ns
Propagation Delay, A or B to APO or BPO	t _{PLH}	C _L = 50pF C _L = 150pF	16 19		27 32		32 38	ns
	t _{PHL}	C _L = 50pF C _L = 150pF	16 19		27 32		32 38	ns
Propagation Delay, API or BPI to APO or BPO	t _{PLH}	C _L = 50pF C _L = 150pF	11 14		18 23		22 28	ns
	t _{PHL}	C _L = 50pF C _L = 150pF	11 14		18 23		22 28	ns
Output Enable Time, G to A or B	t _{PZH}	C _L = 50pF C _L = 150pF	16 19		27 32		32 38	ns
	t _{PZL}	R _L = 1kΩ C _L = 50pF	16 19		27 32		32 38	ns
Output Disable Time, G to A or B	t _{PHZ}	R _L = 1kΩ C _L = 50pF	16		27		32	ns
	t _{PLZ}	R _L = 1kΩ C _L = 50pF	16		27		32	ns
Output Enable Time, DIR to A or B	t _{PZH}	R _L = 1kΩ C _L = 50pF	16 19		27 32		32 38	ns
	t _{PZL}	R _L = 1kΩ C _L = 50pF	16 19		27 32		32 38	ns
Output Disable Time, DIR to A or B	t _{PHZ}	R _L = 1kΩ C _L = 50pF	16		27		32	ns
	t _{PLZ}	R _L = 1kΩ C _L = 50pF	16		27		32	ns
Input Capacitance	C _{IN}			5				pF
Output Capacitance	C _{OUT}	Output Disabled						pF
Power Dissipation Capacitance*	C _{PD}							pF

* C_{PD} determines the no-load dynamic power dissipation: P_D = C_{PD} V_{CC}² f + I_{CC} V_{CC}.

† For AC switching test circuits and timing waveforms see section 2.



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PACKAGE DIMENSIONST-90-20**1. PLASTIC PACKAGES**

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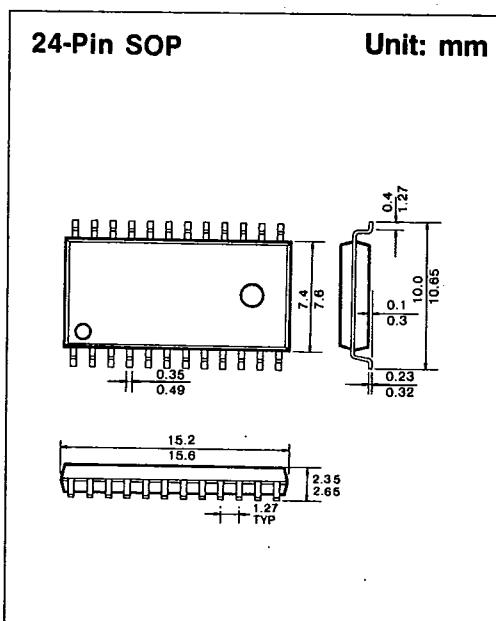
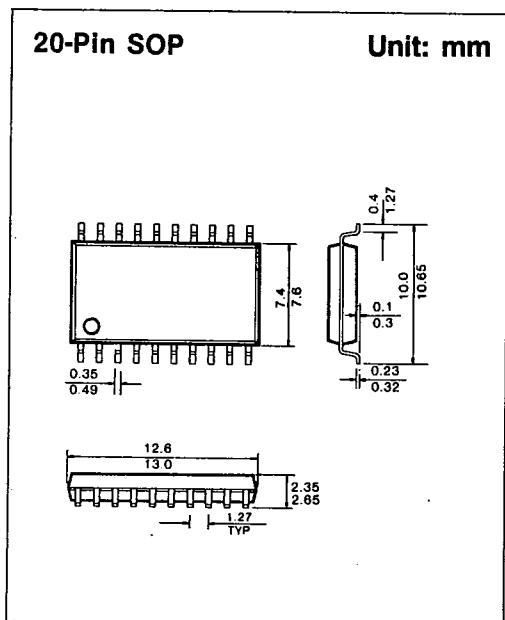
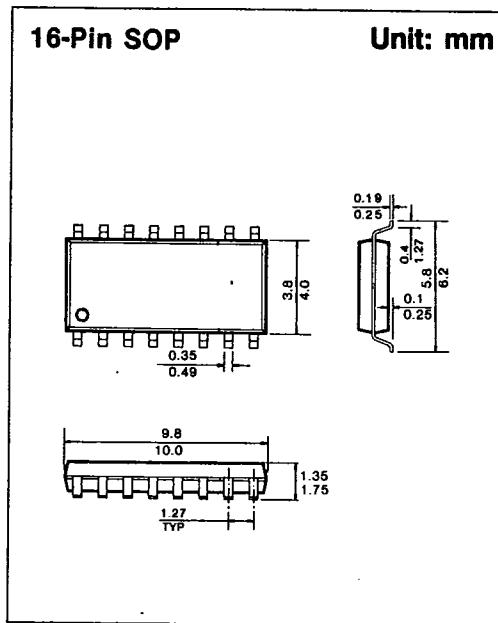
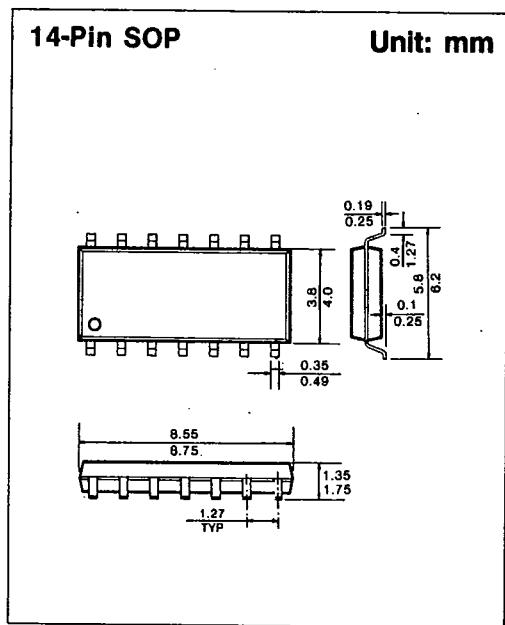


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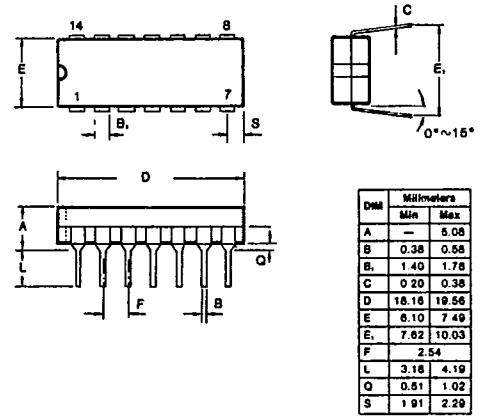
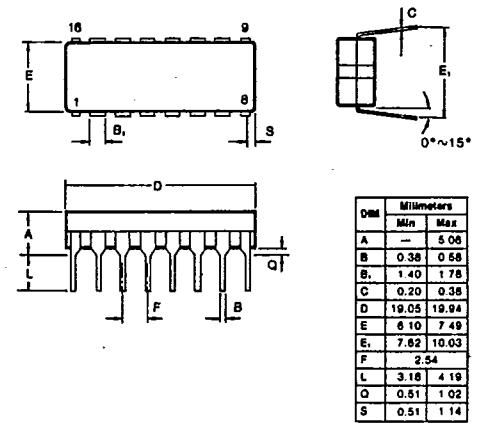
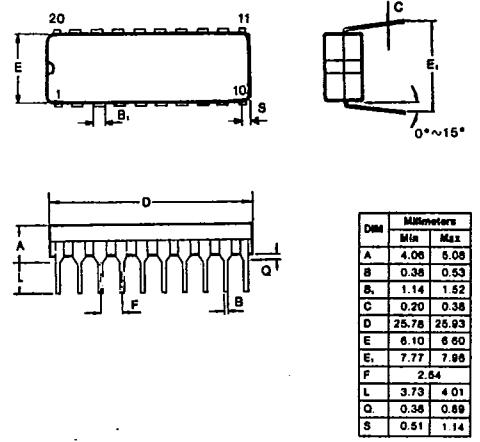
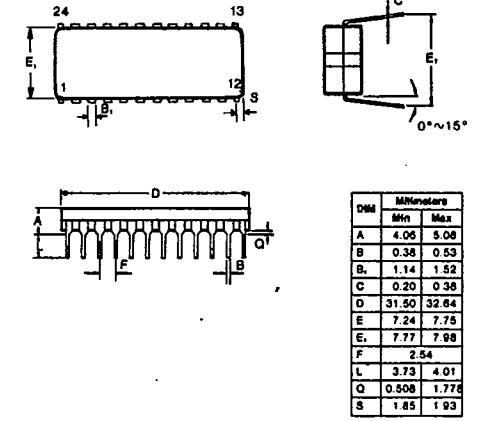
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PACKAGE DIMENSIONS**T-90-20****SAMSUNG SEMICONDUCTOR****1676****A-05**

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PACKAGE DIMENSIONST-90-20**2. CERAMIC PACKAGES****14-Pin Ceramic DIP Units: mm****16-Pin Ceramic DIP Units: mm****20-Pin Ceramic DIP Units: mm****24-Pin Ceramic DIP Units: mm**

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